EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("5525529").PN.	USPAT; USOCR	OR	OFF	2010/01/29 14:02
L8	6510	257/369,408.ccls. or 257/E21.135, E21.466.ccls. or 438/289,301,369,542,559.ccls.	US-PGPUB; USPAT	OR	ON	2010/01/29 14:15
L9	3753	257/369,408.ccls. or 257/E21.135, E21.466.ccls.	US-PGPUB; USPAT	OR	ON	2010/01/29 14:15
L10	3496	257/369,408.ccls.	US-PGPUB; USPAT	OR	ON	2010/01/29 14:16
L11	261	257/E21.135,E21.466.ccls.	US-PGPUB; USPAT	OR	ON	2010/01/29 15:49
L12	2888	438/289,301,369,542,559.ccls.	US-PGPUB; USPAT	OR	ON	2010/01/29 15:54
S1	4	("20020074612" | "5439831" | "5525529" | "5719424").PN.	US-PGPUB; USPAT	OR	OFF	2009/03/29 14:41
S2	1	("6159813").PN.	USPAT; USOCR	OR	OFF	2009/03/29 14:45
S3	1	("20070093030").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/03/29 14:56
S4	88	(boron with diffusi$4 with reduc$4) and (silicon adj nitride) and source and drain and ((halo or LDD) with implant$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/29 15:01
S5	13	(boron with diffusi$4 with reduc$4) and ((silicon adj nitride) with stress) and source and drain and (halo or LDD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/29 15:27
S6	5	(boron with diffusi$4 with reduc$4) and (silicon adj nitride) and source and drain and ((halo or LDD) with implant$5) and (tensile with strain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/30 11:41
S7	0	(boron with diffusi$4 with reduc$4) and ((silicon adj nitride) with (tensile with strain)) and source and drain and ((halo or LDD) with implant$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/30 11:48

S8	0	(boron with diffusi$4 with reduc$4) and ((silicon adj nitride) with (tensile with strain)) and source and drain	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/30 11:48
S9	102	((silicon adj nitride) with (tensile with strain)) and source and drain	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/30 11:49
S10	12	S9 and ((halo or LDD) with implant $5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/30 11:49
S11	313	(boron with diffus$5) and ((halo or pocket) with implant$5) and (FET or MOSFET or PFET or NFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/31 11:47
S12	93	(boron with diffus$5) and ((halo or pocket) with implant$5) and (FET or MOSFET or PFET or NFET) and (stress or strain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/31 11:48
S13	13	("5525529").URPN.	USPAT	OR	OFF	2009/03/31 12:08
S14	1312	(silicon adj nitride) with tensile with stress	US-PGPUB; USPAT	OR	OFF	2009/03/31 14:25
S15	381	S14 and gate and source and drain and spacer	US-PGPUB; USPAT	OR	OFF	2009/03/31 14:25
S16	2	"20070093030"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/31 16:03
S17	2	wo-2005064665-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/31 16:05
S18	2	ep-1692717-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/31 16:07

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L16	1	((boron with diffusion) and stress$3 and (anneal$3 or heat$3) and (CMOS or pFET or nFET or PMOS or NMOS or FET) and (lateral or horizontal) and (vertical or longitudinal) and direction and gate).CLM.	US-PGPUB; UPAD	OR	ON	2010/01/29 17:19
L17	1	((boron with diffusion with concentration with profile) and stress$3 and (anneal$3 or heat$3) and (CMOS or pFET or nFET or PMOS or NMOS or FET) and (source $drain or S/D) and (lateral or horizontal) and (vertical or longitudinal) and direction and gate).CLM.	US-PGPUB; UPAD	OR	ON	2010/01/29 17:20
L18	1	((boron with diffusion with profile) and stress$3 and (anneal$3 or heat$3) and (CMOS or pFET or nFET or PMOS or NMOS or FET) and (source$drain or S/D) and (lateral or horizontal) and (vertical or longitudinal) and direction and gate).CLM.	US-PGPUB; UPAD	OR	ON	2010/01/29 17:20
L19	1	((boron with diffusion) and stress$3 and (anneal$3 or heat$3) and (CMOS or pFET or nFET or PMOS or NMOS or FET) and (source$drain or S/ D) and (lateral or horizontal) and (vertical or longitudinal) and direction and gate).CLM.	US-PGPUB; UPAD	OR	ON	2010/01/29 17:21
L20	1	((boron with diffusion) and stress$3 and (anneal$3 or heat$3) and (CMOS or pFET or nFET or PMOS or NMOS or FET) and (lateral or horizontal) and (vertical or longitudinal) and gate).CLM.	US-PGPUB; UPAD	OR	ON	2010/01/29 17:22

1/29/2010 5:22:34 PM
C:\ Documents and Settings\ asarkar\ My Documents\ EAST\ Workspaces\ 10-596249.wsp